

M1F THRU M7F

SMAF Plastic-Encapsulate Diodes

General Purpose Rectifier

Features

- •lo
- •VRRM 50V-1000V
- High surge current capability

1A

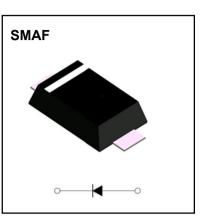
- •Glass passivated chip
- Polarity: Color band denotes cathode

Applications

Rectifier

Marking

• M1F-M7F : M1-M7



Limiting Values (Absolute Maximum Rating)

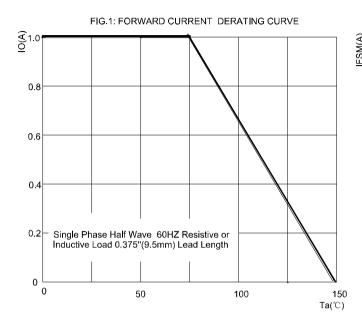
ltem	Symbol	Unit	Conditions	М						
			Conditions	1F	2F	3F	4F	5F	6F	7F
Repetitive Peak Reverse Voltage	V _{RRM}	V		50	100	200	400	600	800	1000
Maximum RMS Voltage	VRMS	V		35	70	140	280	420	560	700
Average Forward Current	I _{F(AV)}	А	60Hz Half-sine wave, Resistance load, Ta=75 $^\circ\!\!\!\!\!^\circ$	1						
Surge(Non-repetitive)Forward Current	I _{FSM}	А	60Hz Half-sine wave,1 cycle, Ta=25 $^\circ\!\!\!\!\!^\circ\!\!\!\!^\circ\!\!\!\!^\circ$	30						
Junction Temperature	TJ	°C		-55~+ 150						
Storage Temperature	T _{STG}	°C		-55 ~ +150						

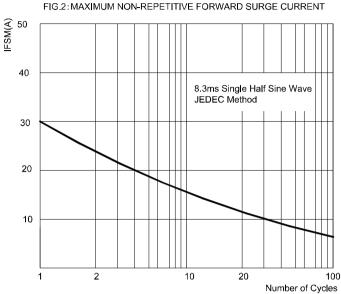
Electrical Characteristics (Ta=25°C Unless otherwise specified)

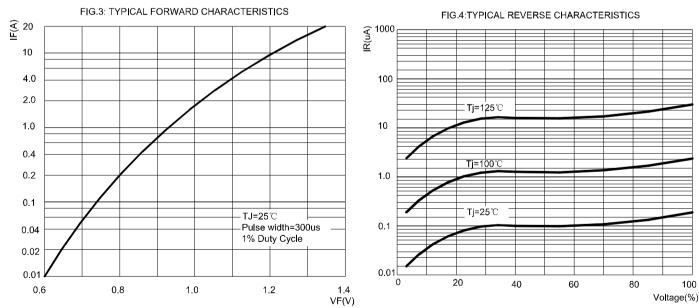
ltem	Symbol	Unit	Test Condition		Мах
Peak Forward Voltage	V _{FM}	V	I _{FM} =1.0A		1.0
Peak Reverse Current	I _{RRM1}	μΑ	V _{RM} =V _{RRM}	Ta=25℃	5
	I RRM2			T _a =125℃	50
Thermal Resistance(Typical)	$R_{\theta_{J}-A}$	°C/W	Between junction and ambient		55
	$R_{ heta J^{-L}}$	0/₩	Between junction and lead		25

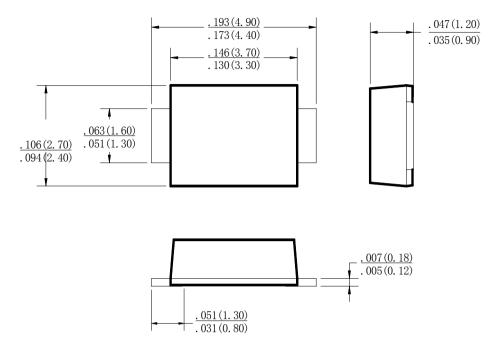
Notes:

Thermal resistance from junction to ambient and from junction to lead mounted on P.C.B. with 0.2" x 0.2" (5.0 mm x 5.0 mm) copper pad areas



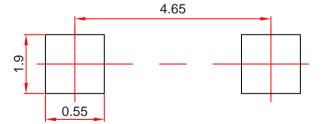






Dimensions in inches and (millimeters)

SMAF Suggested Pad Layout



Note:

1.Controlling dimension:in millimeters.

2.General tolerance:±0.05mm.

3. The pad layout is for reference purposes only.

NOTICE

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High Diode Semiconductor

Reel Taping Specifications For Surface Mount Devices- SMAF

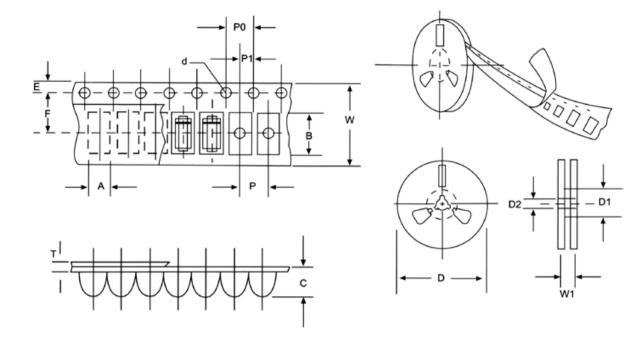


FIG: CONFIGURATION OF SURFACE MOUNTED DEVICES TAPING

ITEM	SYMBOL	SMAF mm(inch)
Carrier width	A	2.83+0.1(0.112+0.004)
Carrier length	В	4.90+0.1(0.193+0.004)
Carrier depth	С	1.45+0.1(0.057+0.004)
Sprocket hole	d	1.55+0.05(0.061+0.002)
Reel outside diameter	D	178+2.0(7.0+0.079)
Reel inner diameter	D1	54±1.0(2.13±0.039)
Feed hole diameter	D2	13+0.5(0.512+0.020)
Strocket hole position	E	1.75+0.1(0.069+0.004)
Punch hole position	F	5.5+0.05(0.217+0.002)
Punch hole pitch	Р	4.0+0.1(0.157+0.004)
Sprocket hole pitch	P0	4.0+0.1(0.157+0.004)
Embossment center	P1	2.0+0.1(0.079+0.004)
Totall tape thickness	Т	0.23-0.29(0.009-0.011)
Tape width	W	12.0+0.1(0.472+0.004)
Reel width	W1	16.8+2.0(0.661+0.079)

NOTE: Devices are packde in accordance with EIA standard RS-481-A and specification given above.

High Diode Semiconductor

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